TRANSISTOR (PNP) **Plastic-Encapsulate Transistor**

FEATURES

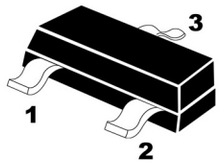
- Power dissipation

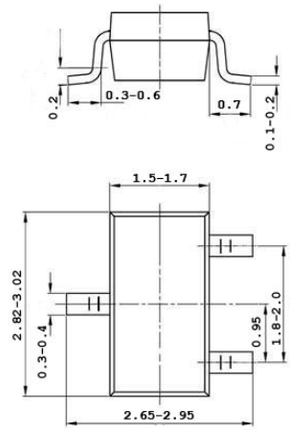
  P_{CM}: 0.2W (Tamb=25℃)

MARKING : AKQ , AKR

SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR





Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

MAXIMUM RATINGS

Parameters	Symbols	Value	UNITS
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA
Junction and Storage Temperature	T_J,T_{stg}	-55-150	℃

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-50μA, I_E=0	-80			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-2mA, I_B=0	-80			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-50μA, I_C=0	-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-50V, I_E=0			-0.5	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-4V, I_C=0			-0.5	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-3V, I_C=-100mA	120		390	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.5	V
Transition Frequency	f_T	V_{CE}=-10V, I_C=-50mA		180		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		11		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R
Range	120-270	180-390